## Key Features :

- Frequency : 63.87 MHz
- Input impedance : $0.5 \Omega$

- Noise : 0.4 dB
- Gain : 28.5 dB
- $\mathrm{OIP}_{3}: 26 \mathrm{dBm}$
- Output VSMR : 1.2
- Magnet free
- 6 V single supply
- Applications : MRI, RF telemetry, medical.


## Description :

GLA-01 is a Low Noise Amplifier (LNA) with low input impedance, it is designed to work with $50 \Omega$ source impedance of multi-channel coils. The front end amplifier exhibits superior performance on noise figure, at different source impedance variation caused by different coil loading or by non-ideal coil design. Also, with its wider noise contour map, the front end amplifier can increase its blocked impedance by using higher source impedance design, at the same time, keep its superior signal noise ratio.

Electrical Characteristics ( $\mathrm{Ta}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Symbol | Parameter | Test Conditions | Value |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min | Typical | Max |  |
| $\mathrm{S}_{21}$ | Gain | 63.87 MHz | 28.3 | 28.8 | 29.3 | dB |
| $\Delta \mathrm{G}$ | Gain Variation | $63.87 \mathrm{MHz} \pm 1 \mathrm{MHz}$ | - | - | $\pm 0.1$ | dB |
| RE[Zin] | Input Impedance | 63.87 MHz | 0.4 | 0.5 | 0.6 | $\Omega$ |
| IM[Zin] |  | 63.87 MHz | -2 | 0 | 2 | $\Omega$ |
| $\mathrm{SWR}_{2}$ | Output VSMR | 63.87 MHz | - | - | 1.2 | - |
| $\mathrm{S}_{12}$ | Reverse Isolation | 63.87 MHz | 95 | 100 | - | dB |
| NF | Noise Figure | 63.87 MHz | - | 0.35 | 0.45 | dB |
| $\mathrm{P}_{1 \mathrm{~dB}}$ | Output Power at 1 dB Compression Point | 63.87 MHz | 9.5 | 10 | - | dBm |
| $\mathrm{OIP}_{3}$ | 3 dB Point Output | Each signal channel $\mathrm{P}_{\text {out }}=$ $0 \mathrm{dBm}, 1 \mathrm{MHz}$ isolation | 22 | 26 | - | dBm |
| $\mathrm{Idd}_{\text {d }}$ | Consumption Current | $\mathrm{V}_{\text {dd }}=6 \mathrm{~V}$ |  | 18 | 20 | mA |
| $\mathrm{V}_{\text {dd }}$ | Supply Operating Voltage |  | 5.9 | 6 | 30 | V |

Absolute Maximum Ratings ( $\mathbf{T a}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Parameter | Unit | Value | Remark |
| :---: | :---: | :---: | :---: |
| Supply Voltage | V | +30 V |  |
| Input Signal Power | dBm | 15 dBm |  |
| Operating Temperature | ${ }^{\circ} \mathrm{C}$ | $-55^{\sim}+125^{\circ} \mathrm{C}$ |  |
| Sintering Temperature | ${ }^{\circ} \mathrm{C}$ | $-40^{\sim}+150^{\circ} \mathrm{C}$ |  |
| Storage Temperature | ${ }^{\circ} \mathrm{C}$ | $-65{ }^{\sim}+150^{\circ} \mathrm{C}$ |  |

[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

[^0]
## Typical Performance

## $S_{21}$ Curve



Noise Curve


IM[Zin] Curve


Phase Curve

$S_{22}$ Curve

$S_{12}$ Curve


OIP ${ }_{3}$ Curve

$P_{1 d \mathrm{~B}}$ Curve


Stability Curve


Chip Dimensions (Unit : $\mu \mathrm{m}$ )


## Chip Layout Diagram



| Lead | 1 | 2 | 3 | 4 |
| :---: | :---: | :---: | :---: | :---: |
| Use | IN | NC $/ \mathrm{V}_{\mathrm{dd}}$ | OUT/ $\mathrm{V}_{\mathrm{dd}}$ | GND |


[^0]:    Advanced Microsystems Technology reserves the right to make change of data and information in the datasheet without prior notice
    Please refer to https://www.advancedmicrosystemstech.com for update information.

